

MOS Capacitor Displacement Damage Dose (DDD) Dosimeter

Wednesday, 14 November 2012 16:50 (20 minutes)

On the characterization by experiments and simulation of the possibilities of nanometric MOS capacitors for DDD dosimetry.

Primary author: Dr PALOMO PINTO, Fco.Rogelio (University of Sevilla, School of Engineering)

Co-authors: Mr FERNÁNDEZ-MARTÍNEZ, Pablo (Centro Nacional de Microelectrónica Barcelona CSIC); Dr HIDALGO VILLENA, Salvador (Centro Nacional de Microelectrónica Barcelona CSIC)

Presenter: Dr PALOMO PINTO, Fco.Rogelio (University of Sevilla, School of Engineering)

Session Classification: Defect and Material Characterization

Track Classification: Microscopic Defects and Material Characterization